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Kind regards,

Team Nexperia

# PEMH20; PUMH20

NPN/NPN resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$ 

Rev. 04 — 15 November 2009

**Product data sheet** 

### 1. Product profile

### 1.1 General description

NPN/NPN resistor-equipped transistors.

Table 1. Product overview

Type number			NPN/PNP	PNP/PNP
	NXP	JEITA	complement	complement
PEMH20	SOT666	-	PEMD20	PEMB20
PUMH20	SOT363	SC-88	PUMD20	PUMB20

#### 1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

### 1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

#### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	50	V
Io	output current (DC)		-	-	100	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	



### 2. Pinning information

Table 3. Pinning

Table 5.	i iiiiiiig		
Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	6 5 4
3	output (collector) TR2		
4	GND (emitter) TR2		R1 R2
5	input (base) TR2		TR1
6	output (collector) TR1	001aab555	R2 R1 1 2 3 sym663
			sym063

### 3. Ordering information

Table 4. Ordering information

Type number	Package	Package		
	Name	Description	Version	
PEMH20	-	plastic surface mounted package; 6 leads	SOT666	
PUMH20	SC-88	plastic surface mounted package; 6 leads	SOT363	

### 4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
PEMH20	6K
PUMH20	H7*

- [1] \* = -: made in Hong Kong
  - \* = p: made in Hong Kong
  - \* = t: made in Malaysia
  - \* = W: made in China

### 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
$V_{CBO}$	collector-base voltage	open emitter	-	50	V
$V_{CEO}$	collector-emitter voltage	open base	-	50	V
$V_{EBO}$	emitter-base voltage	open collector	-	10	V
VI	input voltage				
	positive		-	+12	V
	negative		-	-10	V
Io	output current (DC)		-	100	mA
I <sub>CM</sub>	peak collector current		-	100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$			
	SOT363		<u>[1]</u> -	200	mW
	SOT666		[1][2] _	200	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
Per device	)				
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$			
	SOT363		<u>[1]</u> -	300	mW
	SOT666		[1][2] _	300	mW

<sup>[1]</sup> Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.

### 6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
ui(j-a)	thermal resistance from junction to ambient	in free air				
	SOT363		<u>[1]</u> -	-	625	K/W
	SOT666		[1][2] _	-	625	K/W
Per devic	e					
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air				
	SOT363		<u>[1]</u> -	-	416	K/W
	SOT666		[1][2]	-	416	K/W

<sup>[1]</sup> Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

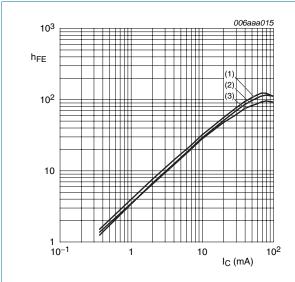
### 7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I <sub>CEO</sub>	collector-emitter	$V_{CE} = 30 \text{ V}; I_B = 0 \text{ A}$	-	-	1	μΑ
	cut-off current	$V_{CE} = 30 \text{ V; } I_{B} = 0 \text{ A;}$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	2	mA
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 20 \text{ mA}$	30	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	150	mV
V <sub>I(off)</sub>	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 1 \text{ mA}$	-	1.2	0.5	V
V <sub>I(on)</sub>	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 20 \text{ mA}$	2	1.6	-	V
R1	bias resistor1 (input)		1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	2.5	pF

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.



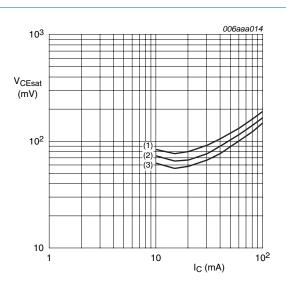
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 1. DC current gain as a function of collector current; typical values



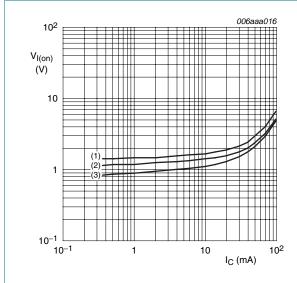
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 2. Collector-emitter saturation voltage as a function of collector current; typical values



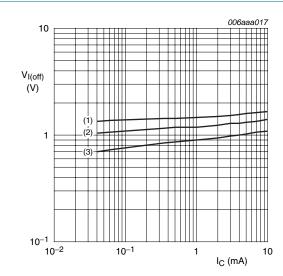
$$V_{CE} = 0.3 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \,^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 3. On-state input voltage as a function of collector current; typical values



$$V_{CE} = 5 V$$

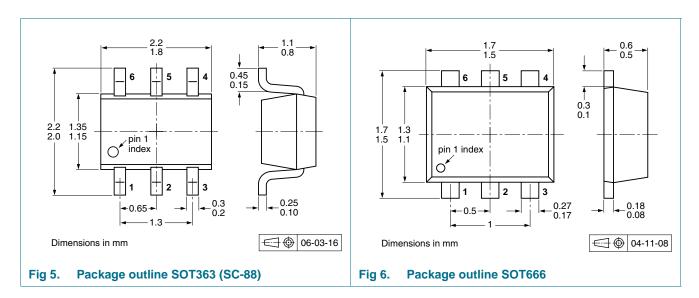
(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 4. Off-state input voltage as a function of collector current; typical values

### 8. Package outline



### 9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing q	uantity		
			3000	4000	8000	10000
PEMH20	SOT666	2 mm pitch, 8 mm tape and reel	-	-	-315	-
		4 mm pitch, 8 mm tape and reel	-	-115	-	-
PUMH20	SOT363	4 mm pitch, 8 mm tape and reel; T1	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	-125	-	-	-165

[1] For further information and the availability of packing methods, see <u>Section 12</u>.

[2] T1: normal taping

[3] T2: reverse taping

### 10. Revision history

### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMH20_PUMH20_4	20091115	Product data sheet	-	PEMH20_PUMH20_3
Modifications:	including nev content.	eet was changed to reflect the was changed to reflect the was legal definitions and disclated the change outline SOT363 (SC-	imers. No changes w	
DEMUSO DUMUSO S	20050214	Product data sheet	. updated	DUMU20 2
PEMH20_PUMH20_3	20050214	Product data sneet	•	PUMH20_2
PUMH20_2	20040414	Product specification	-	PUMH20_1
PUMH20_1	20031016	Product specification	-	-

### 11. Legal information

#### 11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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## PEMH20; PUMH20

NPN/NPN resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$ 

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DCX115EK-7-F DTC113EM3T5G NSVMUN5135DW1T1G NSVMUN2237T1G